



# NX3008PBKV

30 V, 220 mA dual P-channel Trench MOSFET

Rev. 1 — 29 July 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

### 1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 1.4 Quick reference data

Table 1. Quick reference data

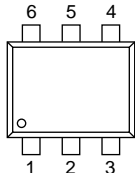
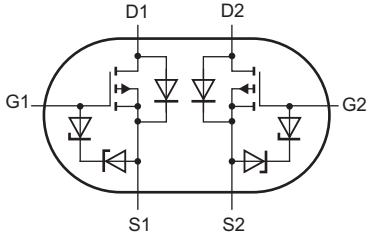
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	-30	V
$V_{GS}$	gate-source voltage		-8	-	8	V
$I_D$	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	-220	mA
<b>Static characteristics (per transistor)</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = -4.5\text{ V}; I_D = -200\text{ mA}; T_j = 25\text{ °C}$	-	2.8	4.1	$\Omega$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	 <p><b>SOT666 (SOT666)</b></p>	 <p>017aaa260</p>
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1		

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
NX3008PBKV	SOT666	plastic surface-mounted package; 6 leads	SOT666

## 4. Marking

**Table 4. Marking codes**

Type number	Marking code <sup>[1]</sup>
NX3008PBKV	AB

[1] % = placeholder for manufacturing site code

## 5. Limiting values

**Table 5. Limiting values**

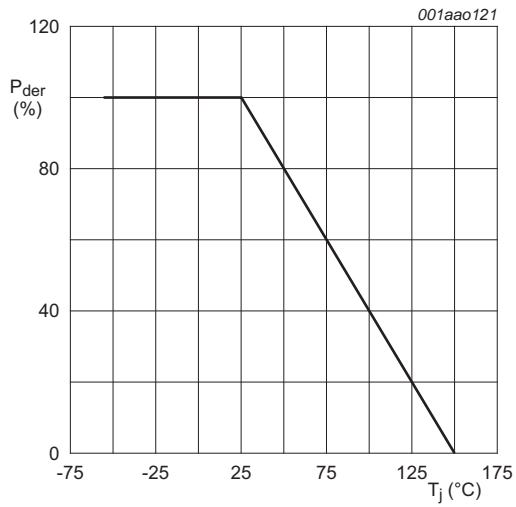
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
<b>Per transistor</b>						
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-30	V	
$V_{GS}$	gate-source voltage		-8	8	V	
$I_D$	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	-220	mA
		$V_{GS} = -4.5\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	-140	mA
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$	-	-0.9	A	
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	330	mW
			[1]	-	390	mW
		$T_{sp} = 25\text{ °C}$	-	-	1090	mW
<b>Per device</b>						
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	500	mW
$T_j$	junction temperature		-55	150	°C	
$T_{amb}$	ambient temperature		-55	150	°C	
$T_{stg}$	storage temperature		-65	150	°C	
<b>Source-drain diode</b>						
$I_S$	source current	$T_{amb} = 25\text{ °C}$	[1]	-	-220	mA
<b>ESD maximum rating</b>						
$V_{ESD}$	electrostatic discharge voltage	HBM	[3]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

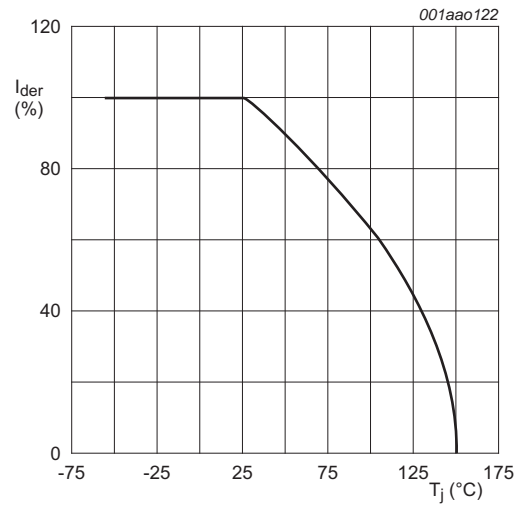
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



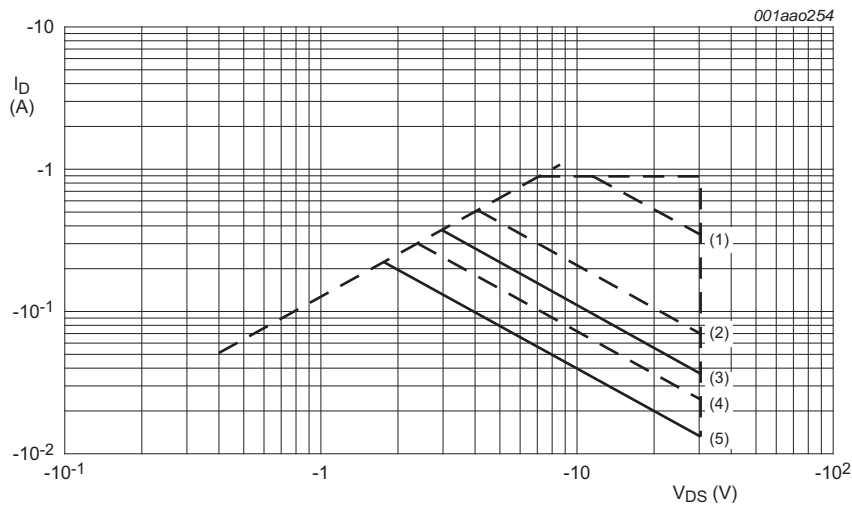
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

**Fig 1. Normalized total power dissipation as a function of junction temperature**



$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\%$$

**Fig 2. Normalized continuous drain current as a function of junction temperature**



$I_{DM}$  is a single pulse

- (1)  $t_p = 1$  ms
- (2)  $t_p = 10$  ms
- (3) DC;  $T_{sp} = 25$  °C
- (4)  $t_p = 100$  ms
- (5) DC;  $T_{amb} = 25$  °C; 1 cm<sup>2</sup> drain mounting pad

**Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage**

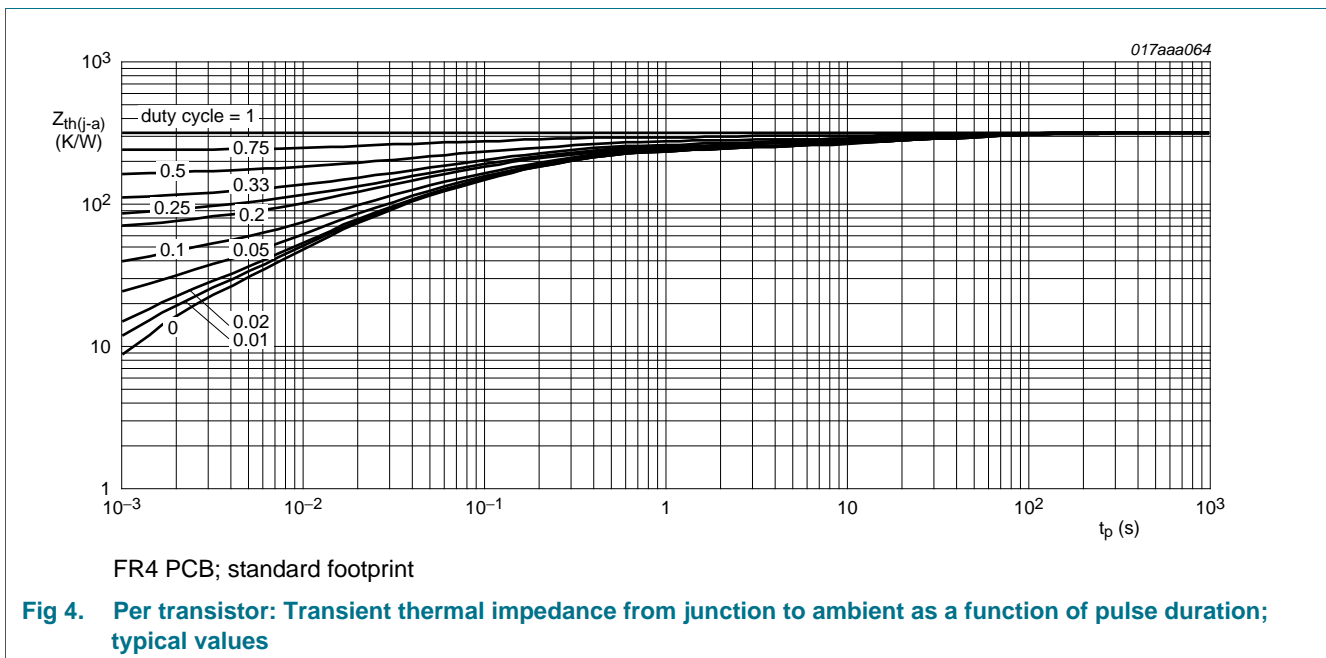
## 6. Thermal characteristics

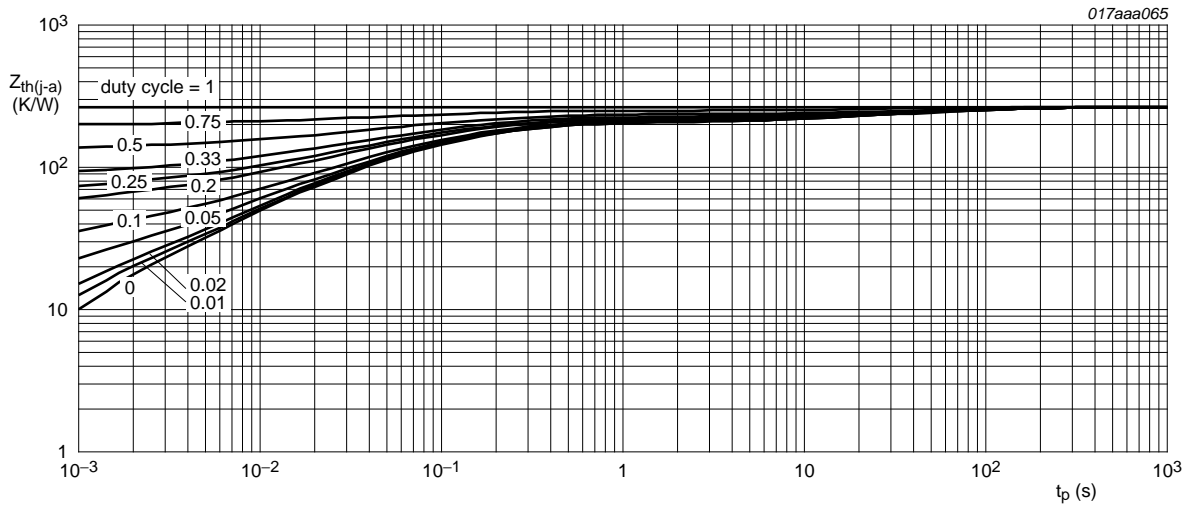
**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per device</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	250	K/W
<b>Per transistor</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	330	380	K/W
			[2] -	280	320	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	115	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.





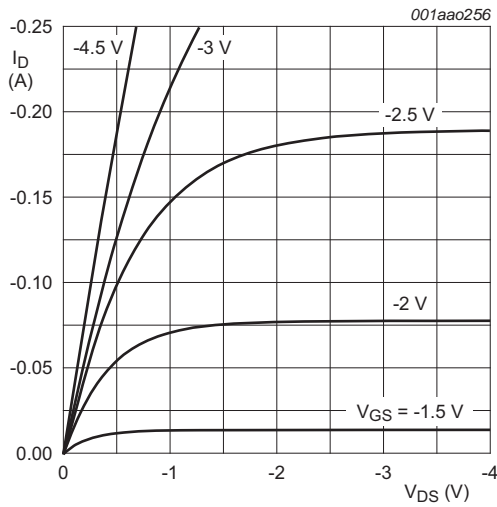
FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

**Fig 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

## 7. Characteristics

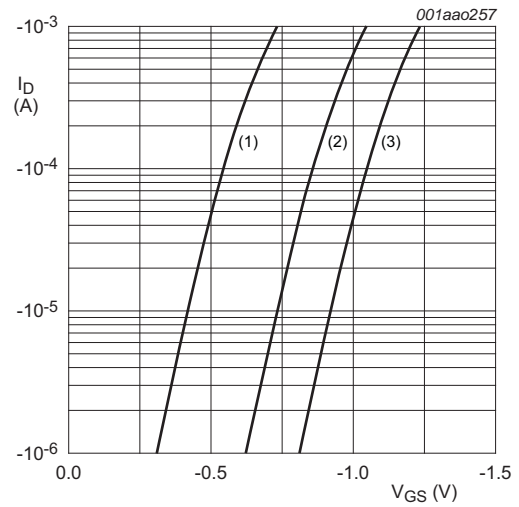
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics (per transistor)</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ }^\circ C$	-0.6	-0.9	-1.1	V
$I_{DSS}$	drain leakage current	$V_{DS} = -30 V$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	-1	$\mu A$
		$V_{DS} = -30 V$ ; $V_{GS} = 0 V$ ; $T_j = 150 \text{ }^\circ C$	-	-	-10	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 8 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-0.2	-1	$\mu A$
		$V_{GS} = -8 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-0.2	-1	$\mu A$
		$V_{GS} = 4.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-10	-	nA
		$V_{GS} = -4.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-10	-	nA
		$V_{GS} = 2.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-1	-	nA
		$V_{GS} = -2.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-1	-	nA
		$V_{GS} = -4.5 V$ ; $I_D = -200 \text{ mA}$ ; $T_j = 25 \text{ }^\circ C$	-	2.8	4.1	$\Omega$
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = -4.5 V$ ; $I_D = -200 \text{ mA}$ ; $T_j = 150 \text{ }^\circ C$	-	5.3	7.8	$\Omega$
		$V_{GS} = -2.5 V$ ; $I_D = -10 \text{ mA}$ ; $T_j = 25 \text{ }^\circ C$	-	5.3	6.5	$\Omega$
		$V_{GS} = -4.5 V$ ; $I_D = -200 \text{ mA}$ ; $T_j = 25 \text{ }^\circ C$	-	160	-	mS
$g_{fs}$	forward transconductance	$V_{DS} = -10 V$ ; $I_D = -200 \text{ mA}$ ; $T_j = 25 \text{ }^\circ C$	-	160	-	mS
<b>Dynamic characteristics (per transistor)</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = -15 V$ ; $I_D = -200 \text{ mA}$ ; $V_{GS} = -4.5 V$ ; $T_j = 25 \text{ }^\circ C$	-	0.55	0.72	nC
$Q_{GS}$	gate-source charge		-	0.23	-	nC
$Q_{GD}$	gate-drain charge		-	0.09	-	nC
$C_{iss}$	input capacitance	$V_{DS} = -15 V$ ; $f = 1 \text{ MHz}$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	31	46	pF
$C_{oss}$	output capacitance		-	6.5	-	pF
$C_{rss}$	reverse transfer capacitance		-	2.3	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = -20 V$ ; $R_L = 250 \Omega$ ; $V_{GS} = -4.5 V$ ; $R_{G(ext)} = 6 \Omega$ ; $T_j = 25 \text{ }^\circ C$	-	19	38	ns
$t_r$	rise time		-	30	-	ns
$t_{d(off)}$	turn-off delay time		-	65	130	ns
$t_f$	fall time		-	38	-	ns
<b>Source-drain diode (per transistor)</b>						
$V_{SD}$	source-drain voltage	$I_S = -200 \text{ mA}$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-0.47	-0.88	-1.2	V



$T_j = 25\text{ }^\circ\text{C}$

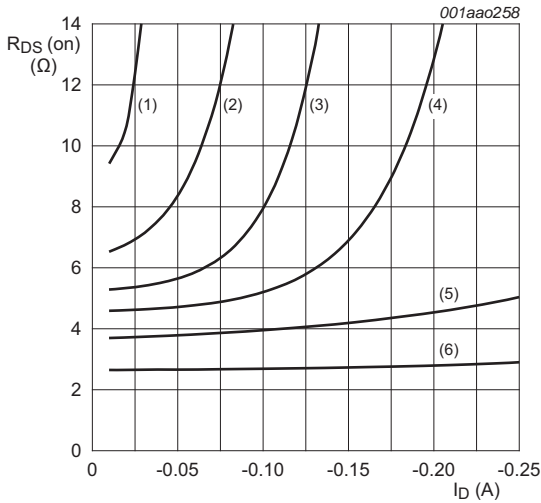
**Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



$T_j = 25\text{ }^\circ\text{C}; V_{DS} = -5\text{ V}$

- (1) minimum values
- (2) typical values
- (3) maximum values

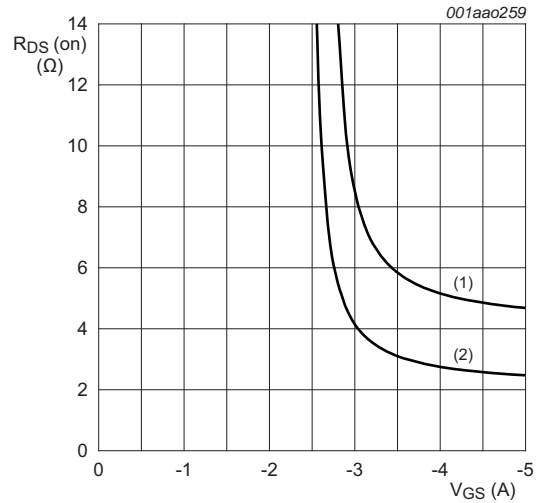
**Fig 7. Sub-threshold drain current as a function of gate-source voltage**



$T_j = 25\text{ }^\circ\text{C}$

- (1)  $V_{GS} = -1.75\text{ V}$
- (2)  $V_{GS} = -2.0\text{ V}$
- (3)  $V_{GS} = -2.25\text{ V}$
- (4)  $V_{GS} = -2.5\text{ V}$
- (5)  $V_{GS} = -3.0\text{ V}$
- (6)  $V_{GS} = -4.5\text{ V}$

**Fig 8. Drain-source on-state resistance as a function of drain current; typical values**

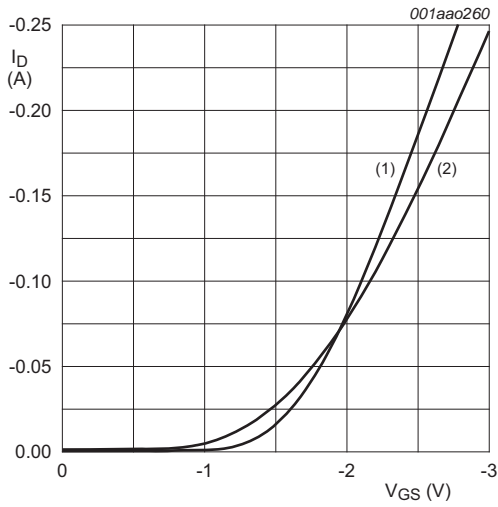


$I_D = -200\text{ mA}$

- (1)  $T_j = 150\text{ }^\circ\text{C}$
- (2)  $T_j = 25\text{ }^\circ\text{C}$

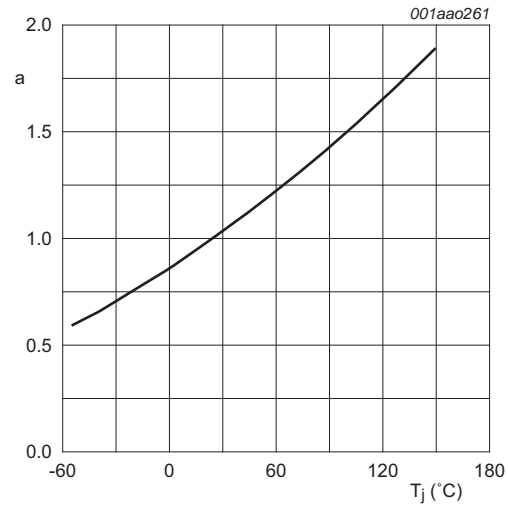
**Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**





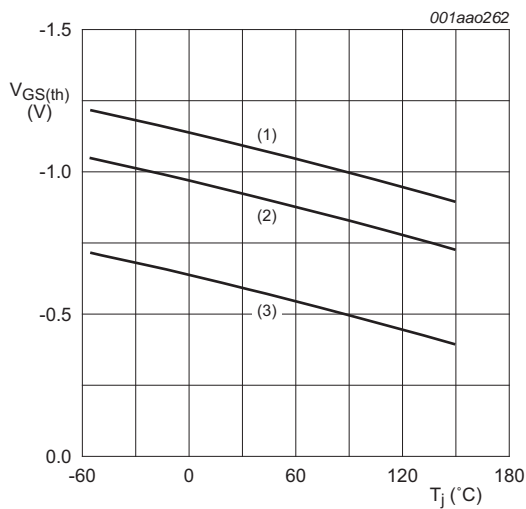
$V_{DS} > I_D \times R_{DS(on)}$   
 (1)  $T_j = 25\text{ }^\circ\text{C}$   
 (2)  $T_j = 150\text{ }^\circ\text{C}$

**Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



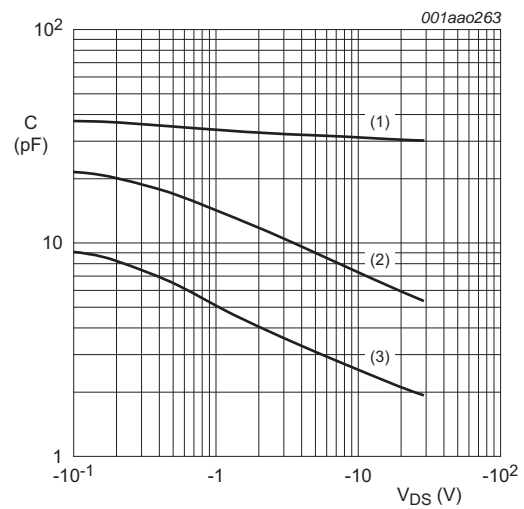
$$a = \frac{R_{DS(on)}}{R_{DS(on)@25^\circ\text{C}}}$$

**Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**



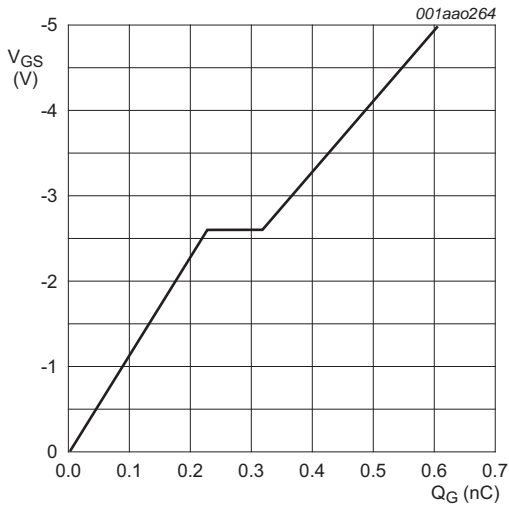
$I_D = -0.25\text{ mA}; V_{DS} = V_{GS}$   
 (1) maximum values  
 (2) typical values  
 (3) minimum values

**Fig 12. Gate-source threshold voltage as a function of junction temperature**



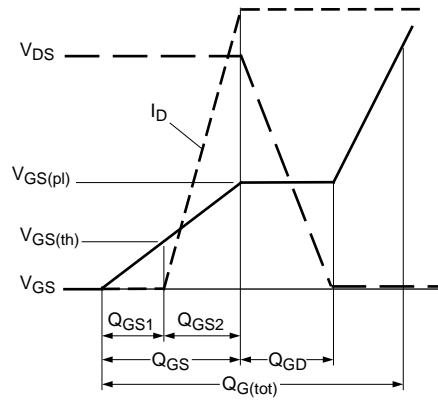
$f = 1\text{ MHz}; V_{GS} = 0\text{ V}$   
 (1)  $C_{iss}$   
 (2)  $C_{oss}$   
 (3)  $C_{rss}$

**Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

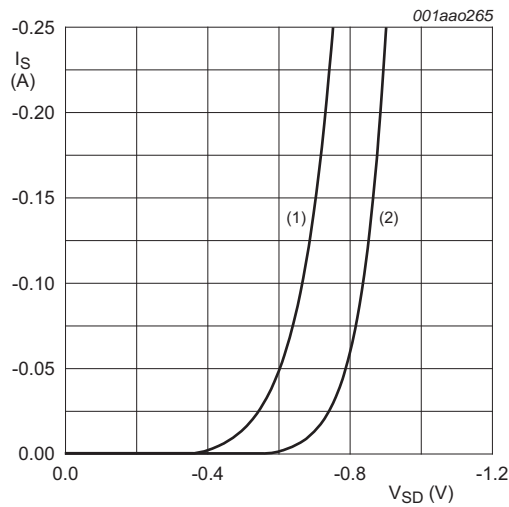


$I_D = -200 \text{ mA}; V_{DS} = -15 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig 14. Gate-source voltage as a function of gate charge; typical values**



**Fig 15. Gate charge waveform definitions**



$V_{GS} = 0 \text{ V}$   
 (1)  $T_j = 150 \text{ }^\circ\text{C}$   
 (2)  $T_j = 25 \text{ }^\circ\text{C}$

**Fig 16. Source current as a function of source-drain voltage; typical values**

## 8. Test information

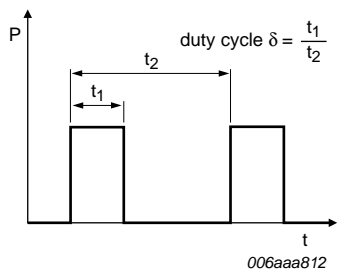


Fig 17. Duty cycle definition

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

**9. Package outline**

Plastic surface-mounted package; 6 leads

SOT666

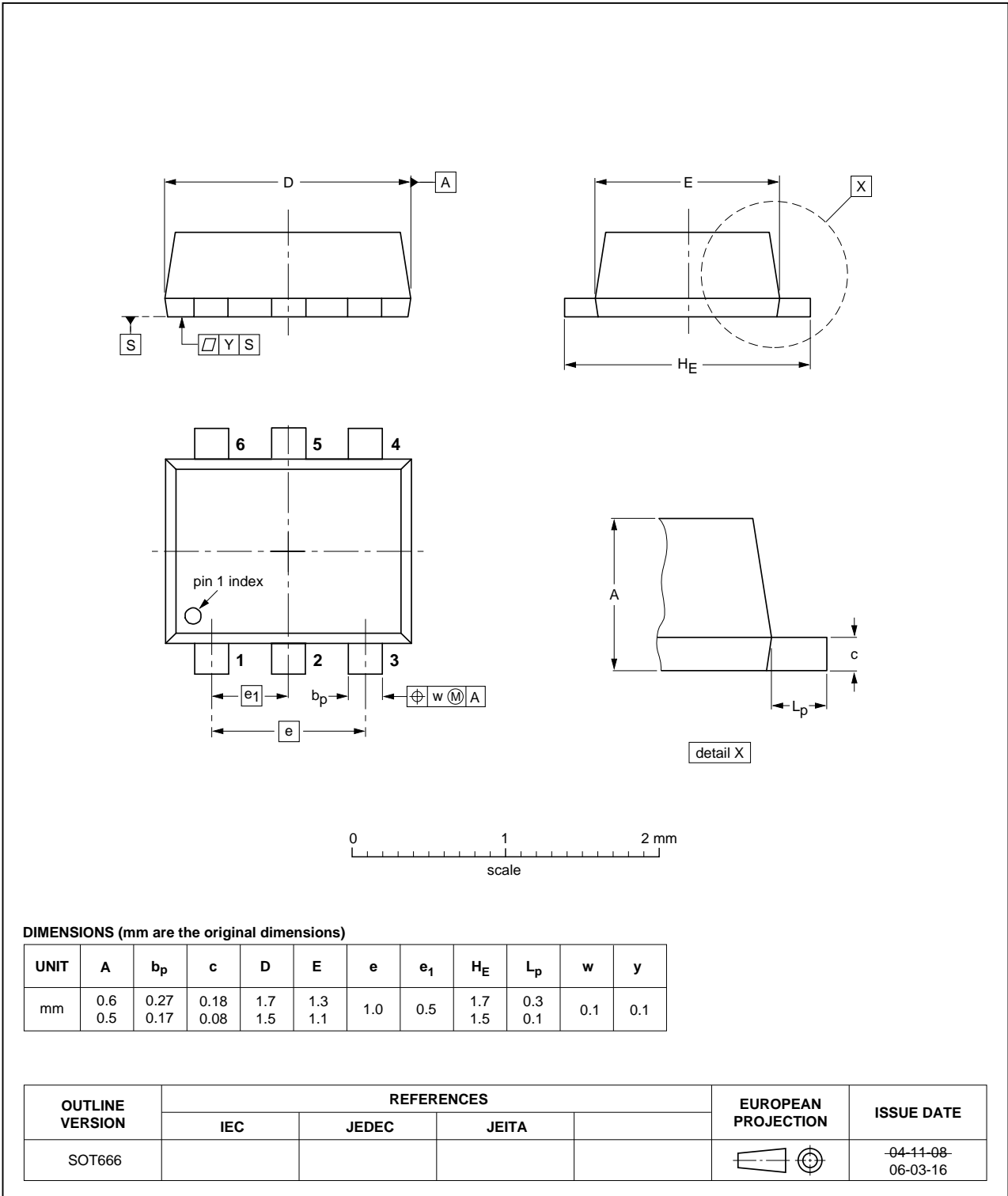
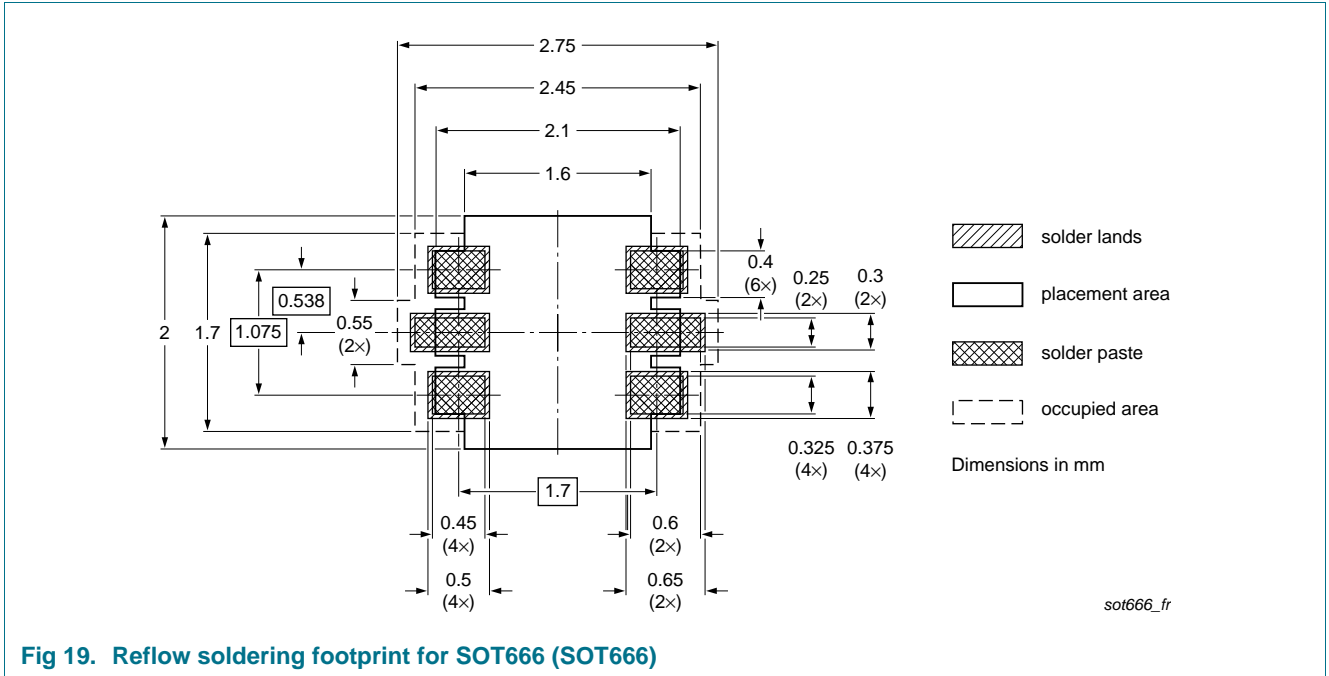


Fig 18. Package outline SOT666 (SOT666)

**10. Soldering**



**Fig 19. Reflow soldering footprint for SOT666 (SOT666)**

## 11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3008PBKV v.1	20110729	Product data sheet	-	-

## 12. Legal information

### 12.1 Data sheet status

Document status <a href="#">[1]</a> <a href="#">[2]</a>	Product status <a href="#">[3]</a>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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 For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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